General Description

The WSD86P10DN56 is the highest performance trench P-ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSD86P10DN56 meet the RoHS and Green Product requirement,100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

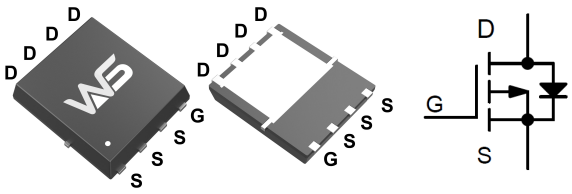
Product Summery

BVDSS	RDSON	ID
-100V	17mΩ	-86A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

DFN5X6_8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, -V_{GS} @ -10V[1]	-86	A
I_D@T_C=100℃	Continuous Drain Current, -V_{GS} @ -10V[1]	-55	A
I_{DM}	Pulsed Drain Current[2]	-280	A
EAS	Single Pulse Avalanche Energy[3]	729	mJ
I_{AS}	Avalanche Current	-54	A
P_D@T_C=25℃	Total Power Dissipation[4]	250	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	0.5	℃/W

Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-100	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.021	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-20A	---	17	28	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.4	-2.1	-2.8	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.08	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-80V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=-80V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-20A	30	---	---	S
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-30V , V_{GS}=-10V , I_D=-20A	---	110	---	nC
Q_{gs}	Gate-Source Charge		---	15	---	
Q_{gd}	Gate-Drain Charge		---	18	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-30V , V_{GS}=-10V , R_G=6Ω, I_D=-10A ,RL=30Ω.	---	27	---	ns
T_r	Rise Time		---	15	---	
$T_{d(off)}$	Turn-Off Delay Time		---	104	---	
T_f	Fall Time		---	57	---	
C_{iss}	Input Capacitance	V_{DS}=-30V , V_{GS}=0V , f=1MHz	---	6105	---	pF
C_{oss}	Output Capacitance		---	728	---	
C_{rss}	Reverse Transfer Capacitance		---	258	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy[5]	V_{DD}=-30V , L=0.5mH , I_{AS}=-54A	300	---	---	mJ

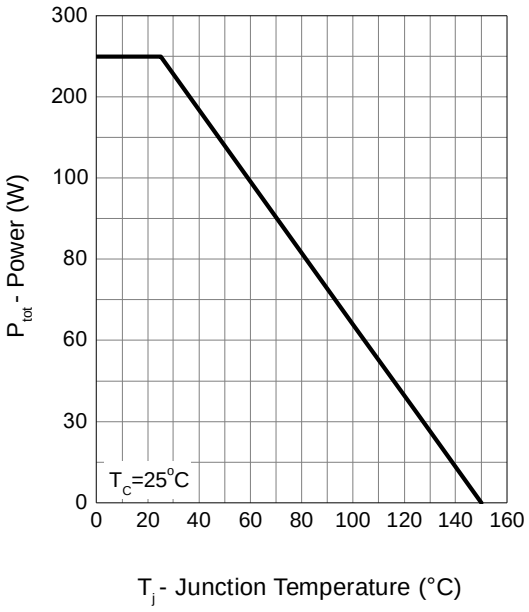
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	-86	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-10A , T_J=25℃	---	---	-1.2	V

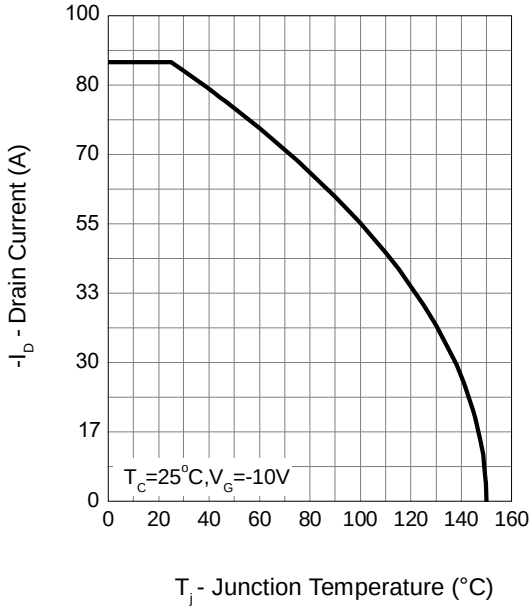
Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper,t≦10sec.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=-30V,V_{GS}=-10V,L=0.5mH,I_{AS}=-54A
4.The power dissipation is limited by 150℃ junction temperature
5.The Min. value is 100% EAS tested guarantee.
6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Operating Characteristics

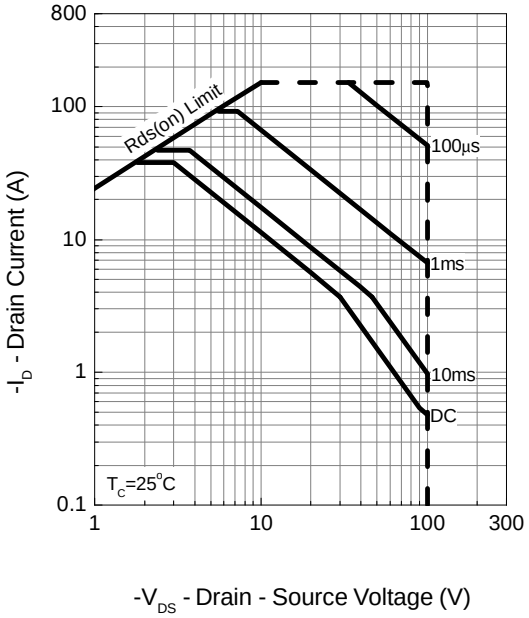
Power Dissipation



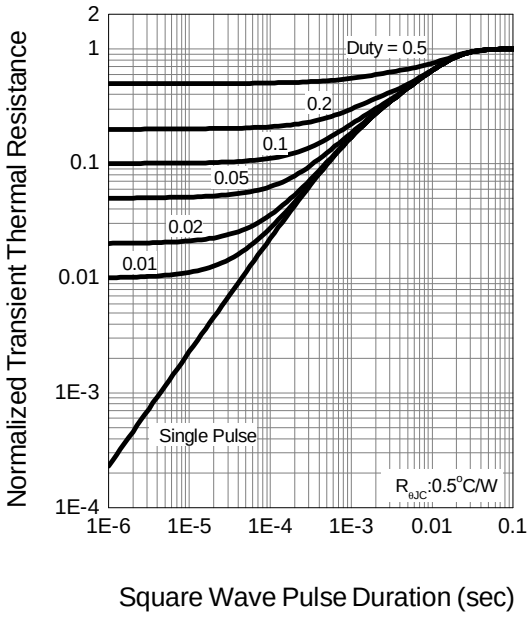
Drain Current



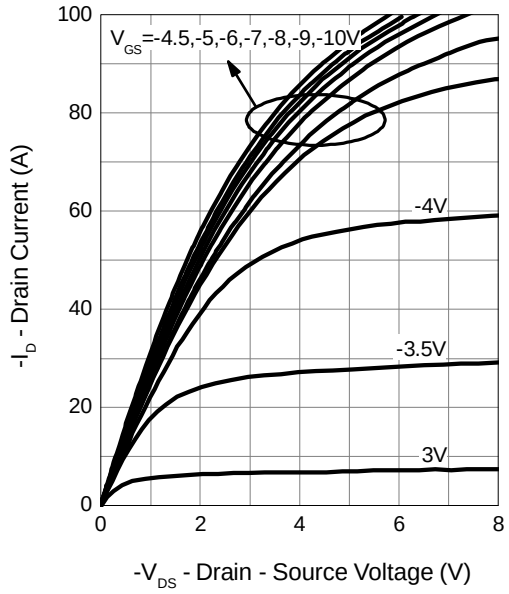
Safe Operation Area



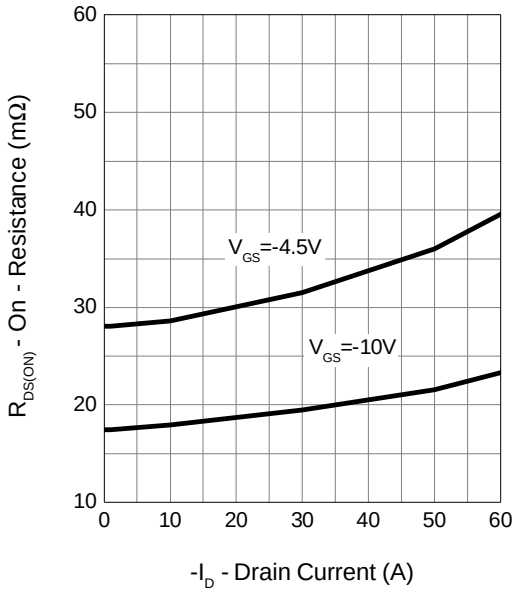
Thermal Transient Impedance



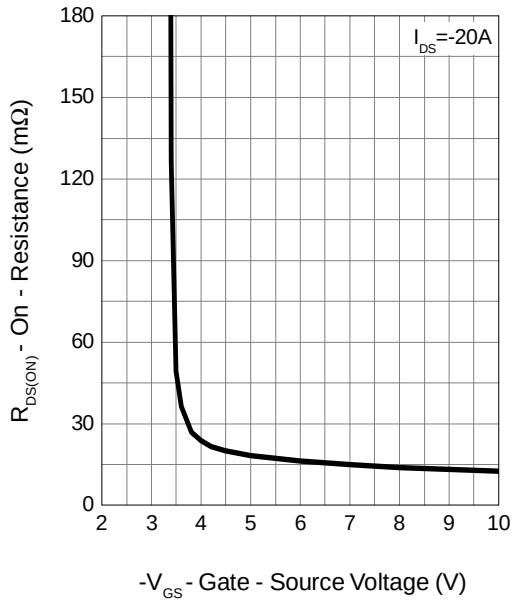
Output Characteristics



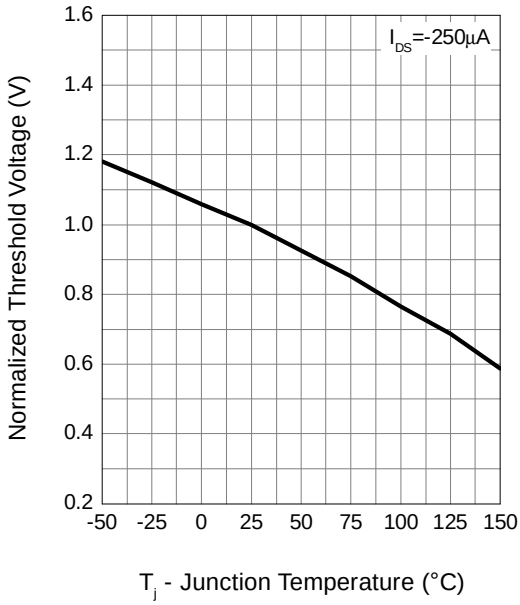
Drain-Source On Resistance



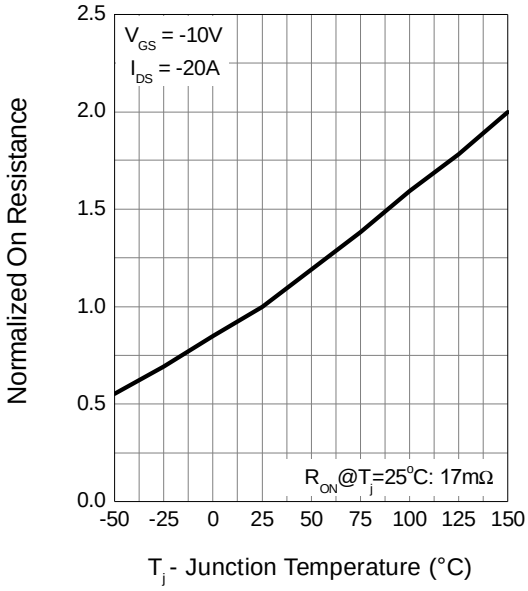
Gate-Source On Resistance



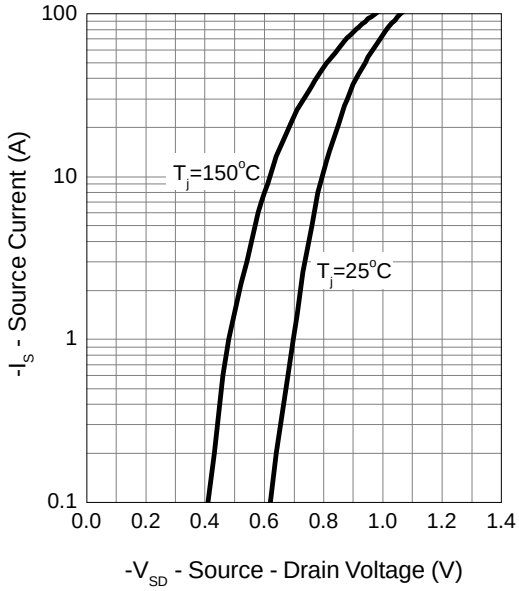
Gate Threshold Voltage



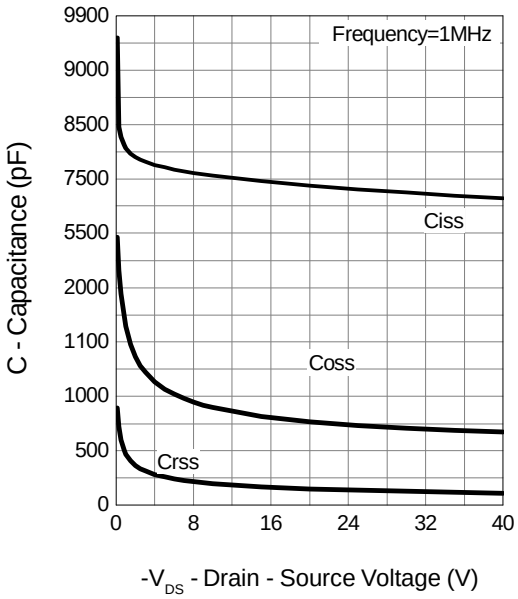
Drain-Source On Resistance



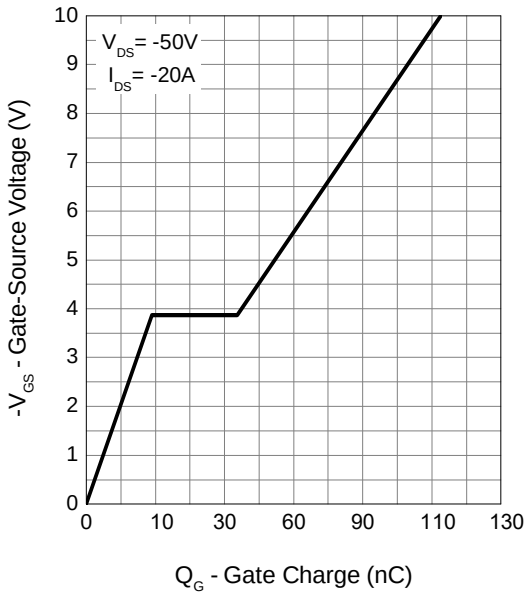
Source-Drain Diode Forward



Capacitance



Gate Charge



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